

KSC1983

High Gain Power Transistor



1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|--|------------|-------|
| V _{CBO} | Collector-Base Voltage | 80 | V |
| V _{CEO} | Collector-Emitter Voltage | 60 | V |
| V _{EBO} | Emitter-Base Voltage | 6 | V |
| I _C | Collector Current | 3 | Α |
| I _B | Base Current | 1 | Α |
| P _C | Collector Dissipation (T _C =25°C) | 30 | W |
| T _J | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | - 55 ~ 150 | °C |

Electrical Characteristics $T_C=25$ °C unless otherwise noted

| Parameter | Test Condition | Min. | Тур. | Max. | Units |
|--|--|---|------|--|--|
| Collector Cut-off Current | $V_{CB} = 80V, I_{E} = 0$ | | | 100 | μΑ |
| Emitter Cut-off Current | $V_{EB} = 6V, I_{C} = 0$ | | | 100 | μΑ |
| Collector-Emitter Breakdown Voltage | $I_C = 25 \text{mA}, I_B = 0$ | 60 | | | V |
| * DC Current Gain | $V_{CE} = 4V, I_{C} = 0.5A$ | 500 | | | |
| * Collector-Emitter Saturation Voltage | $I_C = 2A, I_B = 0.05A$ | | | 1 | V |
| Current Gain Bandwidth Product | $V_{CE} = 12V, I_{C} = 0.2A$ | | 15 | | MHz |
| | Collector Cut-off Current Emitter Cut-off Current Collector-Emitter Breakdown Voltage * DC Current Gain * Collector-Emitter Saturation Voltage | $ \begin{array}{lll} & \text{Collector Cut-off Current} & \text{$V_{\text{CB}} = 80$V}, \ I_{\text{E}} = 0 \\ & \text{Emitter Cut-off Current} & \text{$V_{\text{EB}} = 6$V}, \ I_{\text{C}} = 0 \\ & \text{Collector-Emitter Breakdown Voltage} & I_{\text{C}} = 25\text{mA}, \ I_{\text{B}} = 0 \\ & \text{* DC Current Gain} & \text{$V_{\text{CE}} = 4$V}, \ I_{\text{C}} = 0.5\text{A} \\ & \text{* Collector-Emitter Saturation Voltage} & I_{\text{C}} = 2\text{A}, \ I_{\text{B}} = 0.05\text{A} \\ \end{array} $ | | $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$ | $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$ |

^{*} Pulse Test: PW≤350µs, Duty Cycle≤2% Pulsed

Typical Characteristics

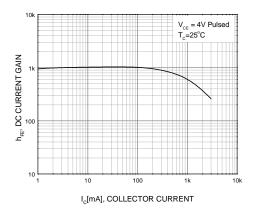


Figure 1. DC current Gain

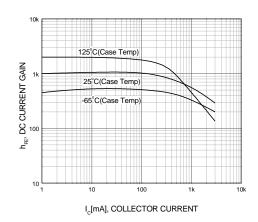


Figure 2. DC current Gain Temperature Characteristic

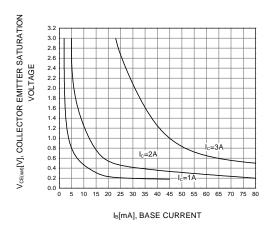


Figure 3. Collector-Emitter Saturation Characteristic

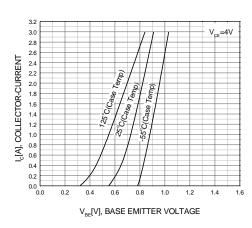


Figure 4. Base-Emitter On Voltage

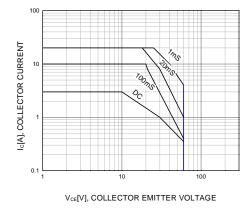


Figure 5. Safe Operating Area

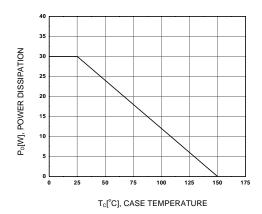
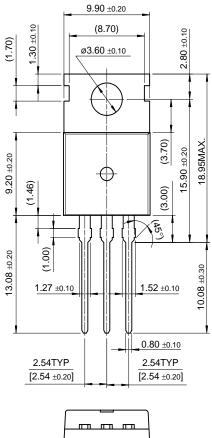


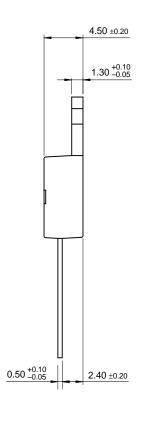
Figure 6. Power Derating

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Package Demensions

TO-220





10.00 ±0.20

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